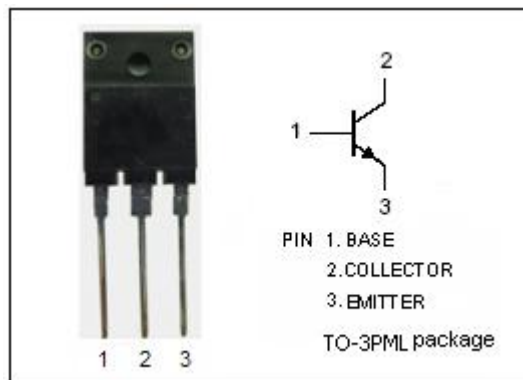


**isc Silicon NPN Power Transistor**
**BUV48BFI**
**DESCRIPTION**

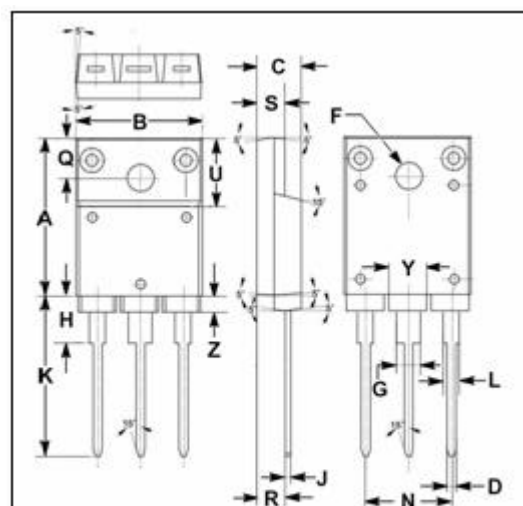
- Collector-Emitter Sustaining Voltage-  
:  $V_{CEO(SUS)} = 600V$  (Min)
- High Current Capability
- Fast Switching Speed
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

**APPLICATIONS**

- Designed for switching and industrial applications from single and three-phase mains.


**Absolute maximum ratings( $T_a = 25^\circ C$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	1200	V
$V_{CEO}$	Collector-Emitter Voltage	600	V
$V_{EBO}$	Emitter-Base Voltage	7	V
$I_C$	Collector Current-Continuous	15	A
$I_{CM}$	Collector Current-Peak $t_p < 5ms$	30	A
$I_B$	Base Current-Continuous	4	A
$I_{BM}$	Base Current-peak $t_p < 5ms$	20	A
$P_C$	Collector Power Dissipation @ $T_c = 25^\circ C$	65	W
$T_j$	Junction Temperature	150	$^\circ C$
$T_{stg}$	Storage Temperature Range	-65~150	$^\circ C$



DIM	mm	
	MIN	MAX
A	19.90	20.10
B	15.75	16.10
C	5.50	5.70
D	0.90	1.10
F	3.30	3.50
G	2.90	3.20
H	5.90	6.10
J	0.595	0.70
K	21.10	22.50
L	1.90	2.25
N	10.80	11.00
Q	4.90	5.10
R	3.75	3.95
S	3.20	3.60
U	9.90	10.10
Y	4.20	4.90
Z	1.90	2.10

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	1.92	$^\circ C/W$

## isc Silicon NPN Power Transistor

## BUV48BFI

## ELECTRICAL CHARACTERISTICS

T<sub>c</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 50mA; I <sub>B</sub> = 0	600		V
V <sub>CER(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 0.5A; L= 2mH; V <sub>clamp</sub> = 1200V R <sub>BE</sub> = 10 Ω	1200		V
V <sub>CE(sat)-1</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 6A; I <sub>B</sub> = 1.5A		1.5	V
V <sub>CE(sat)-2</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 10A; I <sub>B</sub> = 4A		3.0	V
V <sub>BE(sat)-1</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 6A; I <sub>B</sub> = 1.5A		1.5	V
V <sub>BE(sat)-2</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 10A; I <sub>B</sub> = 4A		2.0	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 1200V ; I <sub>B</sub> = 0		0.5	mA
I <sub>CEO</sub>	Collector Cutoff Current	V <sub>CE</sub> = 600V; I <sub>B</sub> = 0		1.0	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 6V; I <sub>C</sub> = 0		1.0	mA

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